



DMN2040LTS

Features

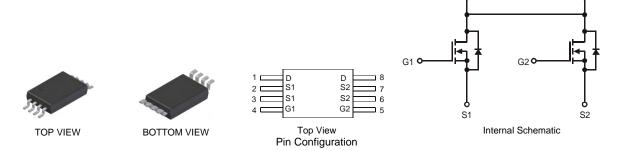
- **Dual N-Channel MOSFET**
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TSSOP-8L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.039 grams (approximate)



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 3)	Steady State	T _A = 25°C T _A = 70°C	I _D	6.7 4.9	А
Pulsed Drain Current (Note 4)		I _{DM}	30	Α	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _D	0.89	W
Thermal Resistance, Junction to Ambient @T _A = 25°C	R _{0JA}	140	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on FR-4 PCB with minimum recommended pad layout.
- 4. Repetitive rating, pulse width limited by junction temperature.

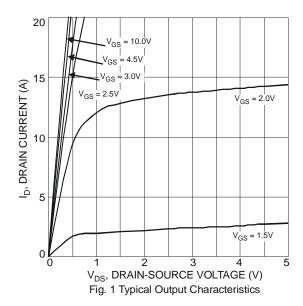


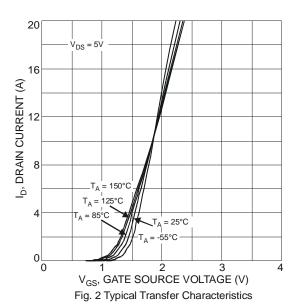
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(th)}	0.5	-	1.2	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D		19	26 36	mΩ	$V_{GS} = 4.5V, I_D = 6.0A$	
Static Drain-Source On-Resistance	R _{DS} (ON)	-	26			$V_{GS} = 2.5V, I_D = 5.2A$	
Forward Transfer Admittance	Y _{fs}	-	8	-	S	$V_{DS} = 10V, I_{D} = 6A$	
Diodes Forward Voltage	V_{SD}	-	0.7	1.2	V	$Is = 1.7A, V_{GS} = 0V$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C _{iss}	ı	570	-	рF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	1	85	-	pF		
Reverse Transfer Capacitance	C_{rss}	•	75	-	рF	-1 = 1.0lvinz	
Gate Resistance	R_{g}	-	1.23	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
SWITCHING CHARACTERISTICS (Note 6)							
Total Gate Charge	Q_{g}	ı	5.2	-	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 7A	
Gate-Source Charge	Q_{gs}	•	0.86	-	nC		
Gate-Drain Charge	Q_{gd}	-	1.25	-	nC		
Turn-On Delay Time	t _{D(on)}	-	5.2	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_L = 1.5\Omega, R_G = 1\Omega$	
Turn-On Rise Time	t _r	-	13.5	-	ns		
Turn-Off Delay Time	t _{D(off)}	-	19.8	-	ns		
Turn-Off Fall Time	t _f	-	6.1	-	ns	1	

Notes: 5. Short duration pulse test used to minimize self-heating effects.

6. Guaranteed by design. Not subject to production testing.







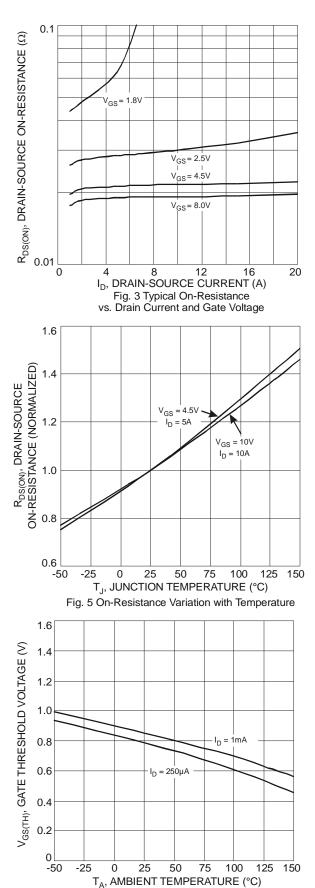


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

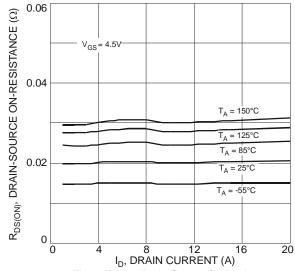


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

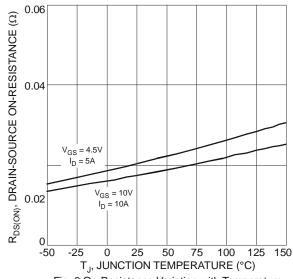


Fig. 6 On-Resistance Variation with Temperature

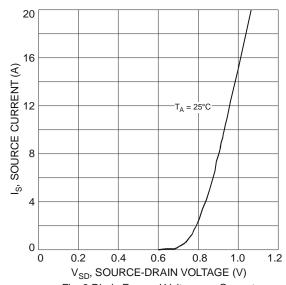
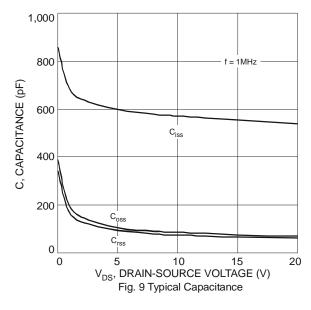


Fig. 8 Diode Forward Voltage vs. Current





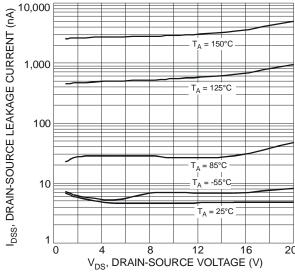
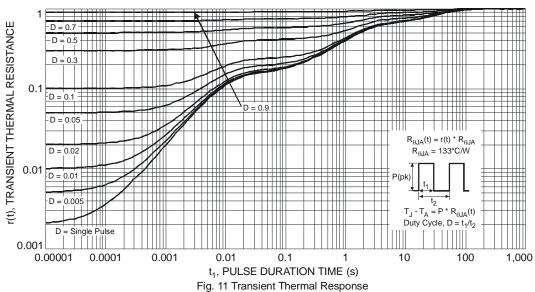


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

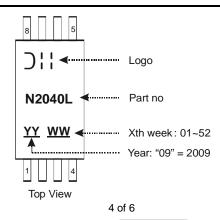


Ordering Information (Note 7)

Part Number	Case	Packaging	
DMN2040LTS-13	TSSOP-8L	2500 / Tape & Reel	

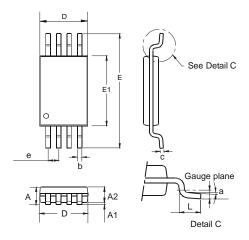
Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



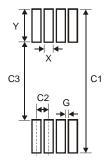


Package Outline Dimensions



	TSSOP-8L				
Dim	Min	Max	Тур		
а	0.09	_	_		
Α	_	1.20	_		
A1	0.05	0.15	_		
A2	0.825	1.025	0.925		
b	0.19	0.30	_		
С	0.09	0.20	_		
D	2.90	3.10	3.025		
е	_	_	0.65		
E	_	_	6.40		
E1	4.30	4.50	4.425		
L	0.45	0.75	0.60		
All	All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.45
Y	1.78
C1	7.72
C2	0.65
C3	4.16
G	0.20



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